

March 2000 Revised June 2005

74VCX164245

Low Voltage 16-Bit Dual Supply Translating Transceiver with 3-STATE Outputs

General Description

The VCX164245 is a dual supply, 16-bit translating transceiver that is designed for two way asynchronous communication between busses at different supply voltages by providing true signal translation. The supply rails consist of $V_{\rm CCB}$, which is the higher potential rail operating at 2.3V to 3.6V and $V_{\rm CCA}$, which is the lower potential rail operating at 1.65V to 2.7V. ($V_{\rm CCA}$ must be less than or equal to $V_{\rm CCB}$ for proper device operation.) This dual supply design allows for translation from 1.8V to 2.5V busses to busses at a higher potential, up to 3.3V.

The Transmit/Receive (T/ \overline{R}) input determines the direction of data flow. Transmit (active-HIGH) enables data from A Ports to B Ports. Receive (active-LOW) enables data from B Ports to A Ports. The Output Enable (\overline{OE}) input, when HIGH, disables both A and B Ports by placing them in a High-Z condition. The A Port interfaces with the lower voltage bus (1.8V - 2.5V). The B Port interfaces with the higher voltage bus (2.7V - 3.3V). Also the VCX164245 is designed so that the control pins (T/ \overline{R}_n , \overline{OE}_n) are supplied by VCCB.

The 74VCX164245 is suitable for mixed voltage applications such as notebook computers using a 1.8V CPU and 3.3V peripheral components. It is fabricated with an Advanced CMOS technology to achieve high speed operation while maintaining low CMOS power dissipation.

Features

- Bidirectional interface between busses ranging from 1.65V to 3.6V
- Supports Live Insertion and Withdrawal (Note 1)
- Static Drive (I_{OH}/I_{OL})
 - ±24 mA @ 3.0V V_{CC}
 - ±18 mA @ 2.3V V_{CC}
 - ±6 mA @ 1.65V V_{CC}
- Uses patented noise/EMI reduction circuitry
- Functionally compatible with 74 series 16245
- Latchup performance exceeds 300 mA
- ESD performance:

Human Body Model >2000V

Machine model >200V

Also packaged in plastic Fine-Pitch Ball Grid Array (FBGA)

Note 1: To ensure the high impedance state during power up or power down, OE_n should be tied to V_{CCB} through a pull up resistor. The minimum value of the resistor is determined by the current sourcing capability of the driver.

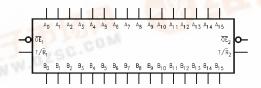
Ordering Code:

Order Number	Package Number	Package Description
74VCX164245G (Note 2)(Note 3)	BGA54A	54-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide
74VCX164245MTD (Note 3)	MTD48	48-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 6.1mm Wide

Note 2: Ordering Code "G" indicates Trays.

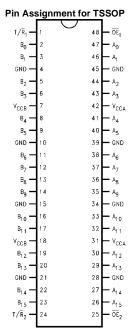
Note 3: Device also available in Tape and Reel. Specify by appending suffix letter "X" to the ordering code.

Logic Diagram

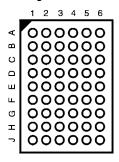




Connection Diagrams



Pin Assignment for FBGA



(Top Through View)

Pin Descriptions

Pin Names	Description
\overline{OE}_n	Output Enable Input (Active LOW)
T/\overline{R}_n	Transmit/Receive Input
A ₀ -A ₁₅	Side A Inputs or 3-STATE Outputs
B ₀ -B ₁₅	Side B Inputs or 3-STATE Outputs
NC	No Connect

FBGA Pin Assignments

	1	2	3	4	5	6
Α	B ₀	NC	T/R ₁	OE ₁	NC	A_0
В	B ₂	B ₁	NC	NC	A ₁	A ₂
С	B ₄	В ₃	V _{CCB}	V_{CCA}	A ₃	A ₄
D	B ₆	B ₅	GND	GND	A ₅	A ₆
E	B ₈	B ₇	GND	GND	A ₇	A ₈
F	B ₁₀	B ₉	GND	GND	A ₉	A ₁₀
G	B ₁₂	B ₁₁	V _{CCB}	V_{CCA}	A ₁₁	A ₁₂
Н	B ₁₄	B ₁₃	NC	NC	A ₁₃	A ₁₄
J	B ₁₅	NC	T/R ₂	OE ₂	NC	A ₁₅

Truth Tables

Inp	uts				
OE ₁	T/R ₁	Outputs			
L	L	Bus B ₀ –B ₇ Data to Bus A ₀ –A ₇			
L	Н	Bus B ₀ -B ₇ Data to Bus A ₀ -A ₇ Bus A ₀ -A ₇ Data to Bus B ₀ -B ₇			
Н	Х	HIGH Z State on A ₀ -A ₇ , B ₀ -B ₇			

Inp	uts					
OE ₂	T/R ₂	Outputs				
L	L	Bus B ₈ –B ₁₅ Data to Bus A ₈ –A ₁₅				
L	Н	Bus A ₈ -A ₁₅ Data to Bus B ₈ -B ₁₅				
Н	X	HIGH-Z State on A ₈ -A ₁₅ , B ₈ -B ₁₅				

H = HIGH Voltage Level

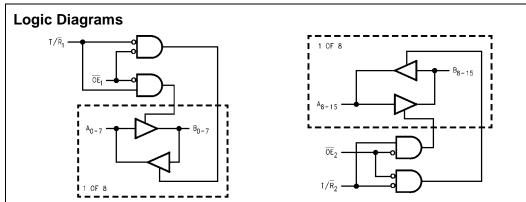
Translator Power Up Sequence Recommendations

To guard against power up problems, some simple guidelines need to be adhered to. The VCX164245 is designed so that the control pins $(T/\overline{R}_n, \overline{OE}_n)$ are supplied by V_{CCB} . Therefore the first recommendation is to begin by powering up the control side of the device, V_{CCB} . The \overline{OE}_n control pins should be ramped with or ahead of V_{CCB} , this will guard against bus contentions and oscillations as all A Port and B Port outputs will be disabled. To ensure the high impedance state during power up or power down, \overline{OE}_n should be tied to V_{CCB} through a pull up resistor. The minimum value of the resistor is determined by the current

sourcing capability of the driver. Second, the T/\overline{R}_n control pins should be placed at logic low (0V) level, this will ensure that the B-side bus pins are configured as inputs to help guard against bus contention and oscillations. B-side Data Inputs should be driven to a valid logic level (0V or V_{CCB}), this will prevent excessive current draw and oscillations. V_{CCA} can then be powered up after V_{CCB} , but should never exceed the V_{CCB} voltage level. Upon completion of these steps the device can then be configured for the users desired operation. Following these steps will help to prevent possible damage to the translator device as well as other system components.

L = LOW Voltage Level
X = Immaterial (HIGH or LOW, inputs may not float)

Z = High Impedance



Please note that these diagrams are provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Supply Voltage

DC V_{CC} or Ground Current

Supply Pin (I_{CC} or Ground)

Storage Temperature (T_{STG})

Absolute Maximum Ratings(Note 4)

Recommended Operating Conditions (Note 6)

V_{CCA}	$-0.5V$ to V_{CCB}
V _{CCB}	-0.5V to 4.6V
DC Input Voltage (V _I)	-0.5V to $+4.6V$
DC Output Voltage (V _{I/O})	
Outputs 3-STATE	-0.5V to +4.6V
Outputs Active (Note 5)	
An	$-0.5V$ to $V_{CCA} + 0.5V$
Bn	$-0.5V$ to $V_{CCB} + 0.5V$
DC Input Diode Current (I _{IK})	
$V_1 < 0V$	−50 mA
DC Output Diode Current (IOK)	
$V_O < 0V$	–50 mA
$V_O > V_{CC}$	+50 mA
DC Output Source/Sink Current	±50 mA
(I_{OH}/I_{OL})	

Power Supply (Note 7)

V_{CCA} 1.65V to 2.7V V_{CCB} 2.3V to 3.6V

Input Voltage (V_I) @ \overline{OE} , T/\overline{R} 0V to V_{CCB}

Input/Output Voltage (V_{I/O})

 $\begin{array}{ccc} A_n & & \text{OV to V}_{CCA} \\ B_n & & \text{OV to V}_{CCB} \end{array}$

Output Current in I_{OH}/I_{OL}

 $\begin{array}{lll} \mbox{V}_{CCA} = 2.3 \mbox{V to } 2.7 \mbox{V} & \pm 18 \mbox{ mA} \\ \mbox{V}_{CCA} = 1.65 \mbox{V to } 1.95 \mbox{V} & \pm 6 \mbox{ mA} \\ \mbox{V}_{CCB} = 3.0 \mbox{V to } 3.6 \mbox{V} & \pm 24 \mbox{ mA} \\ \mbox{V}_{CCB} = 2.3 \mbox{V to } 2.7 \mbox{V} & \pm 18 \mbox{ mA} \\ \end{array}$

Free Air Operating Temperature (T_A) -40°C to +85°C

Minimum Input Edge Rate (Δt/ΔV)

 $V_{IN} = 0.8V$ to 2.0V, $V_{CC} = 3.0V$ 10 ns/V

Note 4: The "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. The device should not be operated at these limits. The parametric values defined in the Electrical Characteristics tables are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Note 5: I_O Absolute Maximum Rating must be observed.

Note 6: Unused inputs or I/O pins must be held HIGH or LOW. They may not float.

Note 7: Operation requires: $V_{CCA} \le V_{CCB}$

DC Electrical Characteristics (1.65V < $V_{CCA} \leq$ 1.95V, 2.3V < $V_{CCB} \leq$ 2.7V)

±100 mA

-65°C to +150°C

Symbol	Parameter		Conditions	V _{CCA} (V)	V _{CCB} (V)	Min	Max	Units
V_{IHA}	HIGH Level Input Voltage	A _n		1.65-1.95	2.3-2.7	0.65 x V _{CC}		V
V_{IHB}		B _n , T/R, OE		1.65-1.95	2.3-2.7	1.6		V
V _{ILA}	LOW Level Input Voltage	A _n		1.6-1.95	2.3-2.7		0.35 x V _{CC}	V
V_{ILB}		B _n , T/R, ŌE		1.65-1.95	2.3-2.7		0.7	V
V _{OHA}	HIGH Level Output Voltag	e	I _{OH} = -100 μA	1.65-1.95	2.3-2.7	V _{CCA} -0.2		V
			$I_{OH} = -6 \text{ mA}$	1.65	2.3-2.7	1.25		V
V _{OHB}	HIGH Level Output Voltag	е	I _{OH} = -100 μA	1.65-1.95	2.3-2.7	V _{CCB} -0.2		V
			I _{OH} = -18 mA	1.65-1.95	2.3	1.7		v
V _{OLA}	LOW Level Output Voltage)	I _{OL} = 100 μA	1.65-1.95	2.3-2.7		0.2	V
			I _{OL} = 6 mA	1.65	2.3-2.7		0.3	v
V _{OLB}	LOW Level Output Voltage)	I _{OL} = 100 μA	1.65-1.95	2.3-2.7		0.2	V
			I _{OL} = 18 mA	1.65-1.95	2.3		0.6	v
II	Input Leakage Current @	OE, T/R	$0V \leq V_I \leq 3.6V$	1.65-1.95	2.3-2.7		±5.0	μА
I _{OZ}	3-STATE Output Leakage		$\frac{OV \le V_O \le 3.6V}{OE} = V_{CCB}$ $V_I = V_{IH} \text{ or } V_{IL}$	1.65–1.95	2.3-2.7		±10	μА
I _{OFF}	Power OFF Leakage Curr	ent	$0 \le (V_I, V_O) \le 3.6V$	0	0		10	μА
I _{CCA} /I _{CCB}	Quiescent Supply Current per supply, V _{CCA} / V _{CCB}	ı	$A_n = V_{CCA}$ or GND B_n , \overline{OE} , & $T/\overline{R} = V_{CCB}$ or GND	1.65-1.95	2.3-2.7		20	μА
			$\begin{aligned} &V_{CCA} \leq A_n \leq 3.6V \\ &V_{CCB} \leq B_n, \ \overline{OE}, \ T/\overline{R} \leq 3.6V \end{aligned}$	1.65–1.95	2.3–2.7		±20	μА
ΔI_{CC}	Increase in I _{CC} per Input, I	B _n , T/R, OE	$V_I = V_{CCB} - 0.6V$	1.65-1.95	2.3-2.7		750	μА
	Increase in I _{CC} per Input,	A _n	$V_I = V_{CCA} - 0.6V$	1.65-1.95	2.3-2.7		750	μА

DC Electrical Characteristics (1.65V < $V_{CCA} \leq$ 1.95V, 3.0V < $V_{CCB} \leq$ 3.6V)

Symbol	Para	meter	Conditions	V _{CCA} (V)	V _{CCB} (V)	Min	Max	Units
V _{IHA}	HIGH Level	A _n		1.65–1.95	3.0-3.6	0.65 x V _{CC}		V
V_{IHB}	Input Voltage	B_n , T/\overline{R} , \overline{OE}		1.65–1.95	3.0-3.6	2.0		V
V _{ILA}	LOW Level	A _n		1.65–1.95	3.0-3.6		0.35 x V _{CC}	V
V_{ILB}	Input Voltage	B_n , T/\overline{R} , \overline{OE}		1.65-1.95	3.0-3.6		0.8	V
V _{OHA}	HIGH Level Output	Voltage	I _{OH} = -100 μA	1.65–1.95	3.0-3.6	V _{CCA} -0.2		V
			$I_{OH} = -6 \text{ mA}$	1.65	3.0-3.6	1.25		•
V _{OHB}	HIGH Level Output	Voltage	I _{OH} = -100 μA	1.65–1.95	3.0-3.6	V _{CCA} -0.2		V
			I _{OH} = -24 mA	1.65–1.95	3.0	2.2		•
V _{OLA}	LOW Level Output	Voltage	$I_{OL} = 100 \mu A$	1.65–1.95	3.0-3.6		0.2	V
			I _{OL} = 6 mA	1.65	3.0-3.6		0.3	•
V_{OLB}	LOW Level Output	Voltage	I _{OL} = 100 μA	1.65–1.95	3.0-3.6		0.2	V
			I _{OL} = 24 mA	1.65–1.95	3.0		0.55	v
l _l	Input Leakage Curr	ent @ OE, T/R	$0V \leq V_I \leq 3.6V$	1.65–1.95	3.0-3.6		±5.0	μΑ
I _{OZ}	3-STATE Output Le	akage	$0V \le V_O \le 3.6V$ $OE^* = V_{CCB}$ $V_I = V_{IH}$ or V_{IL}	1.65–1.95	3.0-3.6		±10	μА
I _{OFF}	Power Off Leakage	Current	$0 \le (V_I, V_O) \le 3.6V$	0	0		10	μΑ
I _{CCA} /I _{CCB}	Quiescent Supply Oper supply, V _{CCA} /V		$A_n = V_{CCA}$ or GND B_n , \overline{OE} , & $T/\overline{R} = V_{CCB}$ or GND	1.65–1.95	3.0-3.6		20	μА
			$\begin{aligned} &V_{CCA} \leq A_n \leq 3.6V \\ &V_{CCB} \leq B_n, \ \overline{OE}, \ T/\overline{R} \leq 3.6V \end{aligned}$	1.65–1.95	3.0-3.6		±20	μА
ΔI_{CC}	Increase in I _{CC} per	Input, B _n , T/R, OE	$V_I = V_{CCB} - 0.6V$	1.65-1.95	3.0-3.6		750	μА
	Increase in I _{CC} per	Input, A _n	$V_I = V_{CCA} - 0.6V$	1.65–1.95	3.0-3.6		750	μА

DC Electrical Characteristics (2.3V < $V_{CCA} \leq$ 2.7V, 3.0V \leq $V_{CCB} \leq$ 3.6V)

Symbol	Parameter		Conditions	V _{CCA} (V)	V _{CCB}	Min	Max	Units
V _{IHA}	HIGH Level Input Voltage	A _n		2.3-2.7	3.0-3.6	1.6		V
V_{IHB}		B _n , T/R, ŌE		2.3-2.7	3.0-3.6	2.0		V
V _{ILA}	LOW Level Input Voltage	A _n		2.3-2.7	3.0-3.6		0.7	V
V_{ILB}		B_n , T/\overline{R} , \overline{OE}		2.3-2.7	3.0-3.6		0.8	V
V _{OHA}	HIGH Level Output Voltag	e	I _{OH} = -100 μA	2.3-2.7	3.0-3.6	V _{CCA} -0.2		V
			I _{OH} = -18 mA	2.3	3.0-3.6	1.7		· ·
V _{OHB}	HIGH Level Output Voltag	е	I _{OH} = -100 μA	2.3–2.7	3.0-3.6	V _{CCB} -0.2		V
			I _{OH} = -24 mA	2.3-2.7	3.0	2.2		, v
V _{OLA}	LOW Level Output Voltage	9	I _{OL} = 100 μA	2.3-2.7	3.0-3.6		0.2	V
			I _{OL} = 18 mA	2.3	3.0-3.6		0.6	· ·
V _{OLB}	LOW Level Output Voltage	9	I _{OL} = 100 μA	2.3–2.7	3.0-3.6		0.2	V
			I _{OL} = 24 mA	2.3-2.7	3.0		0.55	·
I _I	Input Leakage Current @	OE, T/R	$0V \leq V_I \leq 3.6V$	2.3-2.7	3.0-3.6		±5.0	μА
I _{OZ}	3-STATE Output Leakage @ A _n		$\frac{\text{OV} \leq \text{V}_{\text{O}} \leq 3.6\text{V}}{\text{OE}} = \text{V}_{\text{CCA}}$ $\text{V}_{\text{I}} = \text{V}_{\text{IH}} \text{ or V}_{\text{IL}}$	2.3–2.7	3.0–3.6		±10	μΑ
I _{OFF}	Power OFF Leakage Curr	ent	$0 \le (V_1, V_0) \le 3.6V$	0	0		10	μА
I _{CCA} /I _{CCB}	Quiescent Supply Current per supply, V _{CCA} /V _{CCB}	,	$A_n = V_{CCA}$ or GND B_n , \overline{OE} , & $T/\overline{R} = V_{CCB}$ or GND	2.3–2.7	3.0–3.6		20	μА
			$\begin{aligned} & V_{CCA} \leq A_n \leq 3.6V \\ & V_{CCB} \leq B_n, \ \overline{OE}, \ T/\overline{R} \leq 3.6V \end{aligned}$	2.3–2.7	3.0-3.6		±20	μА
Δl _{CC}	Increase in I _{CC} per Input, I	B _n , T/R, OE	V _I = V _{CCB} - 0.6V	2.3-2.7	3.0-3.6		750	μА
	Increase in I _{CC} per Input,	A _n	$V_{I} = V_{CCA} - 0.6V$	2.3-2.7	3.0-3.6		750	μА

AC Electrical Characteristics

0		$C_L = 30$ pF, $R_L = 500\Omega$, $T_A = -40^{\circ}C$ to $+85^{\circ}C$,						
	Parameter	V _{CCA} = 1.65V to 1.95V		V _{CCA} = 1.65V to 1.95V		V _{CCA} = 2.3V to 2.7V V _{CCB} = 3.0V to 3.6V		Units
Symbol	Farameter	V _{CCB} = 2.	V _{CCB} = 2.3V to 2.7V V _{CCB} = 3.0V to 3.6V					
		Min	Max	Min	Max	Min	Max	
t _{PHL} , t _{PLH}	Propagation Delay, A to B	0.8	5.5	0.6	5.1	0.6	4.0	ns
t _{PHL} , t _{PLH}	Propagation Delay, B to A	1.5	5.8	1.5	6.2	0.8	4.4	ns
t_{PZL} , t_{PZH}	Output Enable Time, OE to B	0.8	5.3	0.6	5.1	0.6	4.0	ns
t _{PZL} , t _{PZH}	Output Enable Time, OE to A	1.5	8.3	1.5	8.2	0.8	4.6	ns
t_{PLZ}, t_{PHZ}	Output Disable Time, OE to B	0.8	5.2	0.8	5.6	0.8	4.8	ns
t_{PLZ} , t_{PHZ}	Output Disable Time, OE to A	0.8	4.6	0.8	4.5	0.8	4.4	ns
t _{osHL}	Output to Output Skew		0.5		0.5		0.75	ns
t _{osLH}	(Note 8)		0.5		0.5		0.73	115

Note 8: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{osHL}) or LOW-to-HIGH (t_{osLH}).

Dynamic Switching Characteristics

Symbol	Parameter	Conditions	V _{CCA}	V _{CCB}	T _A = 25°C	Units
Symbol	Farameter	Conditions	(V)	(V)	Typical	Onits
V _{OLP}	Quiet Output Dynamic Peak V _{OL} ,	$C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0V$	1.8	2.5	0.25	
	B to A		1.8	3.3	0.25	V
			2.5	3.3	0.6	
	Quiet Output Dynamic Peak V _{OL} ,	$C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0V$	1.8	2.5	0.6	
	A to B		1.8	3.3	0.8	V
			2.5	3.3	0.8	
V _{OLV}	Quiet Output Dynamic Valley V _{OL} ,	$C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0V$	1.8	2.5	-0.25	
	B to A		1.8	3.3	-0.25	V
			2.5	3.3	-0.6	
	Quiet Output Dynamic Valley V _{OL} ,	$C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0V$	1.8	2.5	-0.6	
	A to B		1.8	3.3	-0.8	V
			2.5	3.3	-0.8	
V _{OHV}	Quiet Output Dynamic Valley V _{OH} ,	$C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0V$	1.8	2.5	1.7	
	A to B		1.8	3.3	2.0	V
			2.5	3.3	2.0	
	Quiet Output Dynamic Valley V _{OH} ,	$C_L = 30 \text{ pF}, V_{IH} = V_{CC}, V_{IL} = 0V$	1.8	2.5	1.3	
	B to A		1.8	3.3	1.3	V
			2.5	3.3	1.7	

Capacitance

Symbol	Parameter	Conditions	$T_A = +25^{\circ}C$	Units
Cynnbon	T diameter	Conditions	Typical	O.III.O
C _{IN}	Input Capacitance	$V_{CCA} = 2.5V$, $V_{CCB} = 3.3V$, $V_{I} = 0V$ or $V_{CCA/B}$	5	pF
C _{I/O}	Input/Output Capacitance	$V_{CCA} = 2.5V$, $V_{CCB} = 3.3V$, $V_{I} = 0V$ or $V_{CCA/B}$	6	pF
C _{PD}	Power Dissipation Capacitance	$V_{CCA} = 2.5V$, $V_{CCB} = 3.3V$, $V_{I} = 0V$ or $V_{CCA/B}$ f = 10 MHz	20	pF

AC Loading and Waveforms

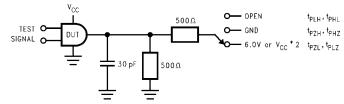


FIGURE 1. AC Test Circuit

TEST	SWITCH		
t _{PLH} , t _{PHL}	OPEN		
t _{PZL} , t _{PLZ}	6V at $V_{CC} = 3.3 \pm 0.3V$; $V_{CC} \times 2$ at $V_{CC} = 2.5 \pm 0.2V$; $1.8V \pm 0.15V$		
t _{PZH} , t _{PHZ}	GND		

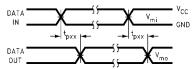


FIGURE 2. Waveform for Inverting and Non-inverting Functions $t_R=t_F \leq \text{2.0 ns, 10\% to 90\%}$

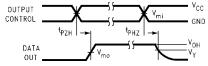


FIGURE 3. 3-STATE Output High Enable and Disable Times for Low Voltage Logic $t_R=t_F \leq 2.0$ ns, 10% to 90%

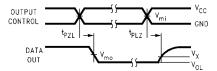
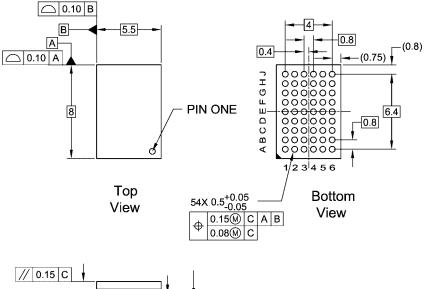


FIGURE 4. 3-STATE Output Low Enable and Disable Times for Low Voltage Logic $t_R=t_F\leq 2.0$ ns, 10% to 90%

Symbol	V _{CC}			
- Cyboi	3.3V ± 0.3V	2.5V ± 0.2V	1.8V ± 0.15V	
V _{mi}	1.5V	V _{CC} /2	V _{CC} /2	
V_{mo}	1.5V	V _{CC} /2	V _{CC} /2	
V _X	V _{OL} + 0.3V	V _{OL} + 0.15V	V _{OL} + 0.15V	
V _Y	V _{OH} – 0.3V	V _{OH} – 0.15V	V _{OH} – 0.15V	

Physical Dimensions inches (millimeters) unless otherwise noted



SEATING PLANE

□ 0.10 C

NOTES:

1.4MAX

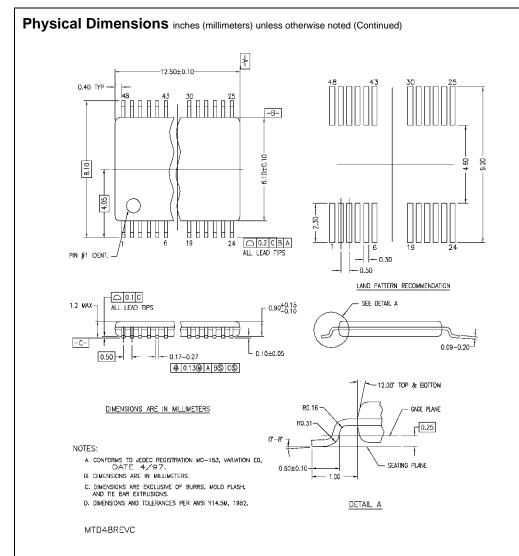
A. THIS PACKAGE CONFORMS TO JEDEC M0-205

0.45 0.35

- B. ALL DIMENSIONS IN MILLIMETERS
- C. LAND PATTERN RECOMMENDATION: NSMD (Non Solder Mask Defined)
 .35MM DIA PADS WITH A SOLDERMASK OPENING OF .45MM CONCENTRIC TO PADS
 D. DRAWING CONFORMS TO ASME Y14.5M-1994

BGA54ArevD

54-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide Package Number BGA54A



48-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 6.1mm Wide Package Number MTD48

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